

isc Silicon PNP Darlington Power Transistor

BDV66/A/B/C

DESCRIPTION

- Collector Current  $-I_C = -16A$
- Collector-Emitter Saturation Voltage:  
:  $V_{CE(sat)} = -2.0V(\text{Max.}) @ I_C = -10A$
- Complement to Type BDV67/A/B/C

APPLICATIONS

- Designed for audio output stages and general amplifier and switching applications

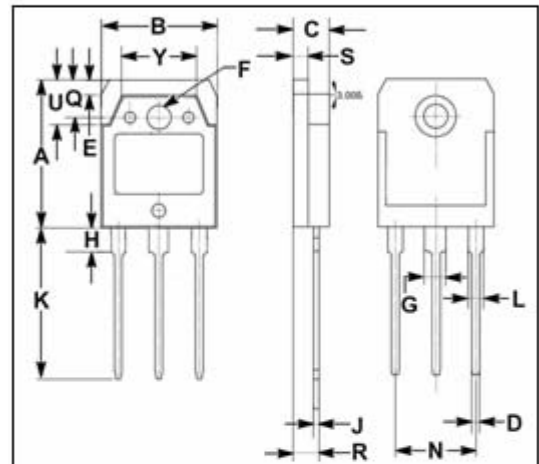
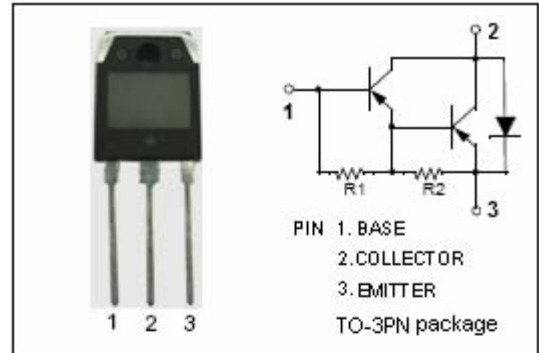
ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{CBO}$	Collector-Base Voltage	BDV66	-80	V
		BDV66A	-100	
		BDV66B	-120	
		BDV66C	-140	
$V_{CEO}$	Collector-Emitter Voltage	BDV66	-60	V
		BDV66A	-80	
		BDV66B	-100	
		BDV66C	-120	
$V_{EBO}$	Emitter-Base Voltage	-5	V	
$I_C$	Collector Current-Continuous	-16	A	
$I_{CM}$	Collector Current-Peak	-20	A	
$I_B$	Base Current-Continuous	-0.5	A	
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	175	W	
$T_J$	Junction Temperature	150	$^\circ\text{C}$	
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.625	$^\circ\text{C/W}$

勝特力材料 886-3-5773766  
 勝特力电子(上海) 86-21-34970699  
 勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

## isc Silicon PNP Darlington Power Transistor

## BDV66/A/B/C

## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
$V_{CE(SUS)}$	Collector-Emitter Sustaining Voltage	BDV66	$I_C = -100\text{mA}; I_B = 0$	-60			V	
		BDV66A		-80				
		BDV66B		-100				
		BDV66C		-120				
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -10\text{A}; I_B = -40\text{mA}$			-2	V		
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -10\text{A}; V_{CE} = -3\text{V}$			-2.5	V		
$I_{CEO}$	Collector Cutoff Current	$V_{CE} = \frac{1}{2}V_{CE0max}; I_B = 0$			-1	mA		
$I_{CBO}$	Collector Cutoff Current	BDV66				-5	mA	
		BDV66A						$V_{CB} = -40\text{V}; I_E = 0; T_J = 150^\circ\text{C}$
		BDV66B						$V_{CB} = -50\text{V}; I_E = 0; T_J = 150^\circ\text{C}$
		BDV66C						$V_{CB} = -60\text{V}; I_E = 0; T_J = 150^\circ\text{C}$
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = V_{CBOmax}; I_E = 0$			-1	mA		
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-5	mA		
$h_{FE}$	DC Current Gain	$I_C = -10\text{A}; V_{CE} = -3\text{V}$	1000					
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f_{test} = 1\text{MHz}$		300		pF		

## Switching times

$t_{on}$	Turn-on Time	$I_C = -10\text{A}; I_{B1} = -I_{B2} = -40\text{mA}; V_{CC} = 12\text{V}$		1		$\mu\text{s}$
$t_{off}$	Turn-off Time			3.5		$\mu\text{s}$